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Docket No.: M4065.1019/P1019  
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:  
Joseph F. Brooks

Patent No.: 7,098,068

Issued: August 29, 2006

For: METHOD OF FORMING A  
CHALCOGENIDE MATERIAL  
CONTAINING DEVICE

**Certificate**  
OCT 10 2006  
**of Correction**

**REQUEST FOR CERTIFICATE OF CORRECTION**  
**PURSUANT TO 37 CFR 1.322**

Attention: Certificate of Correction Branch  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

Upon reviewing the above-identified patent, Patentee noted omissions and typographical errors which should be corrected.

In the Claims, the PTO made the following omissions of text to be corrected:

Claim 42, column 10, line 32, "a layer" should read --a first layer--;

Claim 42, column 10, line 34, "the layer" should read --the first layer--; and

Claim 42, column 10, line 49, "Ge<sub>x</sub>Se<sub>100-x</sub>" should read --Ge<sub>x</sub>Se<sub>100-x</sub>--.

**OCT 12 2006**

In the Other Publications portion of the References Cited section, the PTO made the following errors to be corrected:

“Afifi, M.A.; Labib, H.H.; Fouad, A.A.; Electrical & thermal conductivity of the amorphous semiconductor  $\text{Ge}_x\text{Se}_{1-x}$ , Egypt. J. Phys. 17 (1986) 335-342.”

Should read

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“Fischer-Colbrie, A.; Bienenstock, A.; Fuoss, P.H.; Marcus, M.A., Structure and bonding in photodiffuses amorphous  $\text{Ag-GeSe}_2$  thin films, Phys. Rev. B 38 (1988) 12388-12403.”

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“Gates, B.; Wu, Y.; Y.; Yang, P.; Xia, Y., Single-crystalline nanowires of  $\text{Ag}_2\text{Se}$  can be synthesized by templating against nanowires of trigonal Se, J. Am. Chem. Soc. (2001) currently ASAP.”

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“Mitkiva, M.; Kozicki, M.N., Silver incorporation in Ge-Se glasses used in programmable metallization cell devices, J. Non-Cryst. Solids 299-302 (2002) 1023-1027.”

Should read

--Mitkova, M.; Kozicki, M.N., Silver incorporation in Ge-Se glasses used in programmable metallization cell devices, J. Non-Cryst. Solids 299-302 (2002) 1023-1027.--.

OCT 12 2006

The errors were not in the application as filed or amended by Applicant; accordingly no fee is required.

Transmitted herewith is a proposed Certificate of Correction effecting such amendment. Patentee respectfully solicits the granting of the requested Certificate of Correction.

Dated: October 5, 2006

Respectfully submitted,

By 

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**UNITED STATES PATENT AND TRADEMARK OFFICE  
CERTIFICATE OF CORRECTION**

Page 1 of 2

PATENT NO. : 7,098,068  
APPLICATION NO. : 10/796,109  
ISSUE DATE : August 29, 2006  
INVENTORS : Joseph F. Brooks

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the Claims, the following omissions are corrected:

Claim 42, column 10, line 32, "a layer" should read --a first layer--;

Claim 42, column 10, line 34, "the layer" should read --the first layer--; and

Claim 42, column 10, line 49, "Ge<sub>x</sub>Se<sub>100</sub>." should read --Ge<sub>x</sub>Se<sub>100-x</sub>--.

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Should read

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1 2 2006

--Fischer-Colbrie, A.; Bienenstock, A.; Fuoss, P.H.; Marcus, M.A., Structure and bonding in photodiffused amorphous Ag-GeSe<sub>2</sub> thin films, Phys. Rev. B 38 (1988) 12388-12403.--;

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